

Silicon – Diode Array

FSA2566P

13 Diode Array

60V/350mA

DATASHEET

OEM – Fairchild

Source: Fairchild Databook 1978

**FSA2563M • FSA2563P • FSA2564M • FSA2564P
FSA2565M • FSA2565P • FSA2566M • FSA2566P**
PLANAR AIR-ISOLATED MONOLITHIC DIODE ARRAYS

- C... 3.0 pf (max)
- V_F ... 15 mV (max) @ 10 mA

ABSOLUTE MAXIMUM RATINGS (Note 1)**Temperatures**

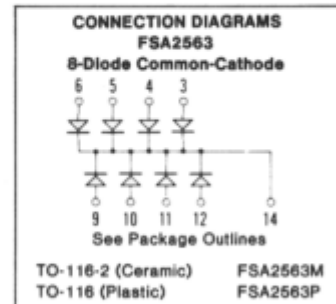
Storage Temperature Range (M Suffix)	-55°C to +200°C
(P Suffix)	-55°C to +150°C
Maximum Junction Operating Temperature	+150°C
Lead Temperature	+260°C

Power Dissipation (Note 2)

Maximum Dissipation per Junction at 25°C Ambient	400 mW
Maximum Dissipation per Package at 25°C Ambient	650 mW
Linear Derating Factor (from 25°C) Junction	3.2 mW/°C
Package	5.2 mW/°C

Maximum Voltage and Currents

WIV	Working Inverse Voltage	40 V
I_F	Continuous Forward Current	350 mA
I_F (surge)	Peak Forward Surge Current	
	Pulse Width = 1.0 s	1.0 A
	Pulse Width = 1.0 μ s	2.0 A

**ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)**

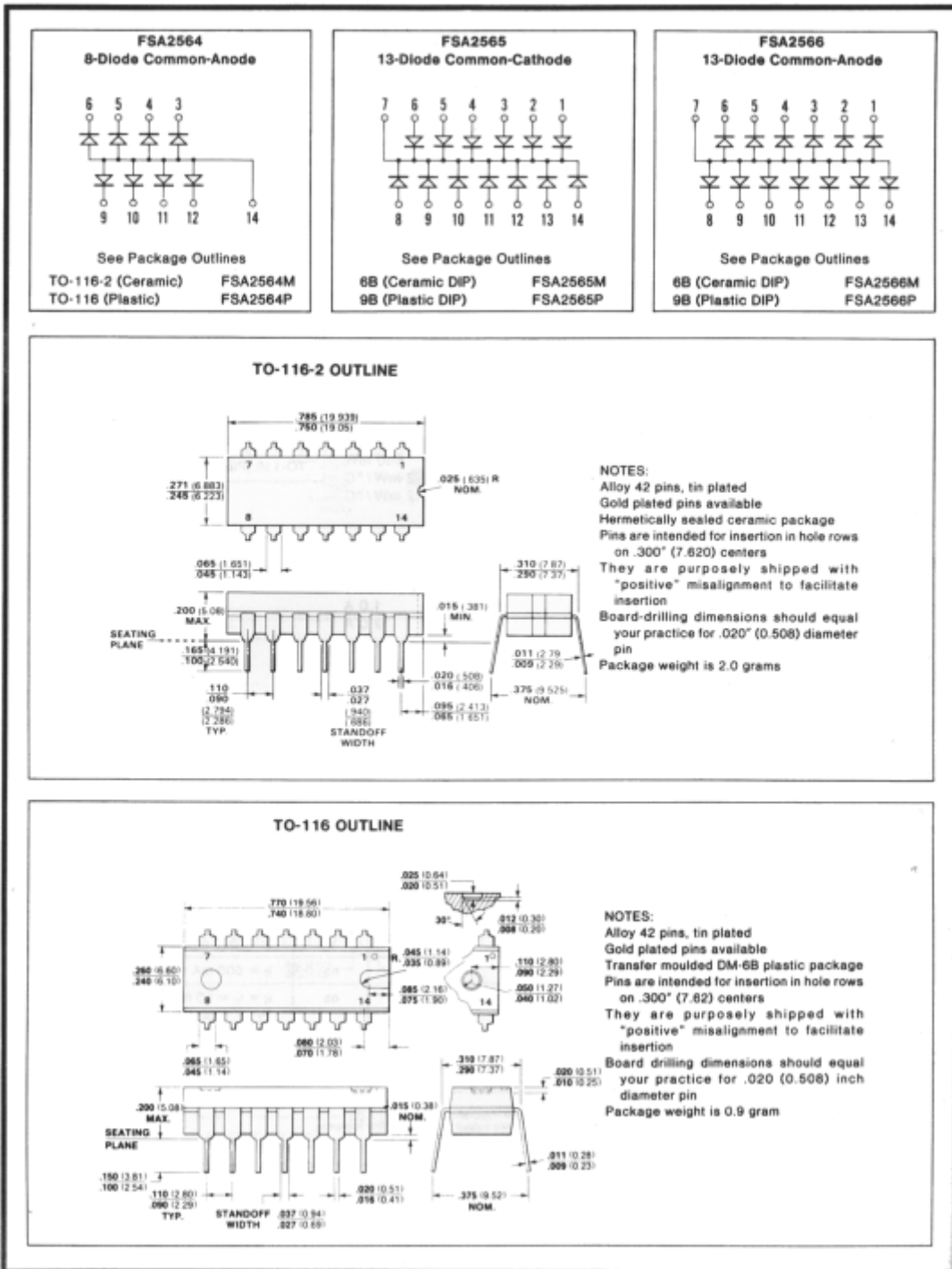
SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
BV	Breakdown Voltage	60		V	$I_R = 10 \mu A$
V_F	Forward Voltage (Note 3)		1.0 1.1 1.3	V	$I_F = 100 \text{ mA}$ $I_F = 200 \text{ mA}$ $I_F = 500 \text{ mA}$
I_R	Reverse Current (Note 4)		100 100	nA μA	$V_R = 40 \text{ V}$ $V_R = 40 \text{ V}, T_A = 125^\circ \text{C}$
C	Capacitance (Note 5)		3	pF	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$
V_{FM}	Peak Forward Voltage (Note 6)		4	V	$I_F = 500 \text{ mA}$
t_{fr}	Forward Recovery Time (Note 6)		40	ns	$I_F = 500 \text{ mA}$
t_{rr}	Reverse Recovery Time (Note 6)		10 50	ns	$I_F = I_R = 10 \text{ mA to } 200 \text{ mA}$ $R_L = 100\Omega, I_{rr} = 0.1 I_F$ $I_F = 500 \text{ mA}, I_r = 50 \text{ mA}$ $R_L = 100\Omega, I_{rr} = 5 \text{ mA}$
ΔV_F	Forward Voltage Match (Note 6)		15	mV	$I_F = 10 \text{ mA}$

NOTES:

- These ratings are limiting values above which life or satisfactory performance may be impaired.
- These are steady state limits. The factory should be consulted on applications involving pulsed or low duty-cycle operation.
- V_F is measured using an 8 μ s pulse.
- See test circuits (Note 6) for measurement of reverse current of an individual diode.
- The capacitance is measured from pin-to-pin across any one of the diodes. The interaction of other diodes is therefore included in the measured value.
- For product family characteristic curves and test circuits, refer to Chapter 4, D15.

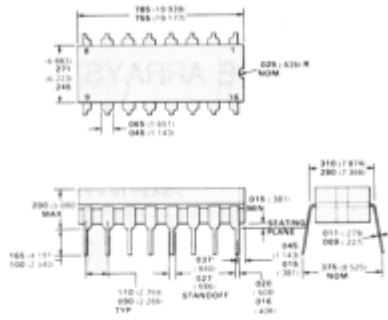
*COMMON ANODE, COMMON CATHODE

FAIRCHILD • DIODE ARRAYS



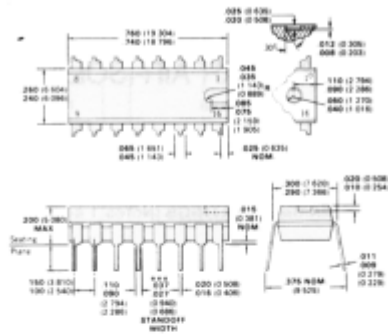
FAIRCHILD • DIODE ARRAYS

6B OUTLINE



- NOTES:**
 Alloy 42 pins, tin plated
 Gold plated pins available
 Hermetically sealed ceramic package
 Pins are intended for insertion in hole rows on .300" centers (7.62)
 They are purposely shipped with "positive" misalignment to facilitate insertion
 Board-drilling dimensions should equal your practice for .020 inch diameter pin (0.51)
 Package weight is 2.0 grams
 *The .037-.027 dimension does not apply to the corner pins

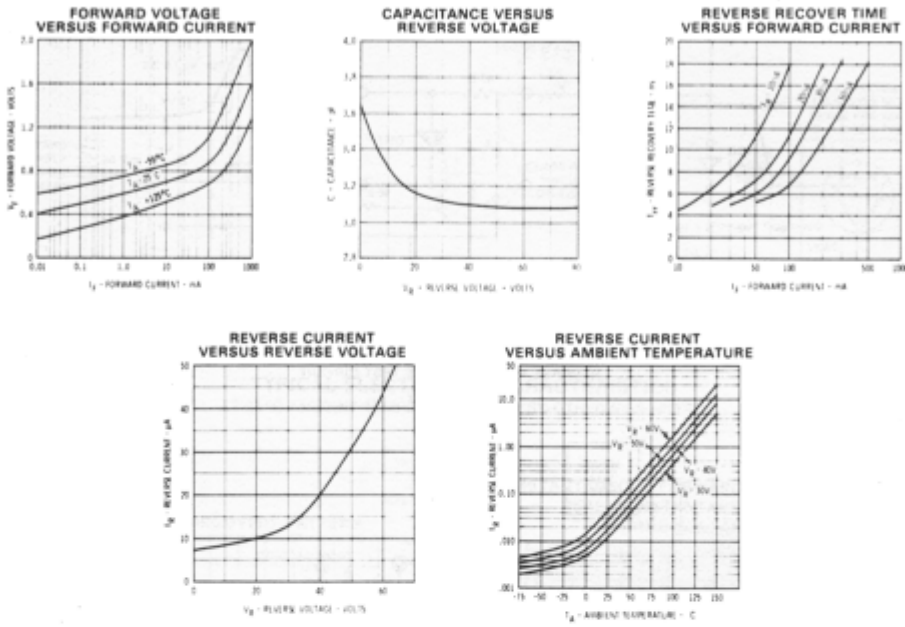
9B OUTLINE



- NOTES:**
 Alloy 42 pins, tin plated
 Gold plated pins available
 Transfer moulded DM-6B plastic package
 Pins are intended for insertion in hole rows on .300" (7.62) centers
 Leads purposely have a "positive" misalignment to facilitate insertion
 Board-drilling dimensions should equal your practice for .020 inch (0.51) diameter pin
 ***The .037-.027 (0.94-0.69) dimension does not apply to the corner pins

CURVE SET NUMBER D15
AIR-ISOLATED MONOLITHIC DIODE ARRAY

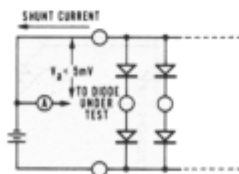
TYPICAL ELECTRICAL CHARACTERISTIC CURVES
 AT 25°C AMBIENT TEMPERATURE UNLESS OTHERWISE NOTED



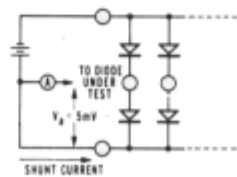
TEST CIRCUITS

To measure reverse current of an individual diode, the following test circuits are used:

COMMON CATHODE DIODES



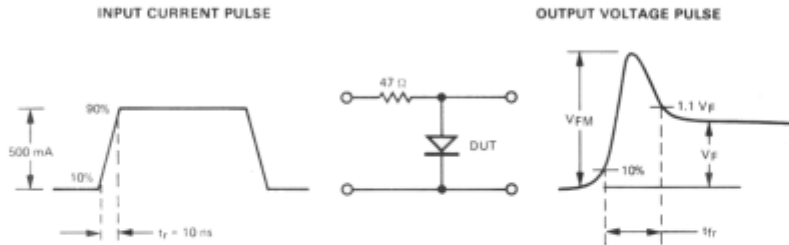
COMMON ANODE DIODES



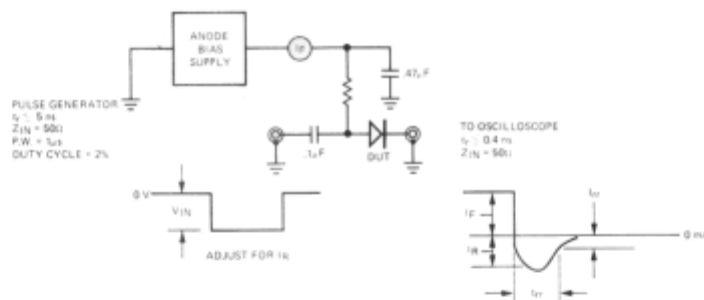
CURVE SET NUMBER D15
AIR-ISOLATED MONOLITHIC DIODE ARRAY

TEST CIRCUITS

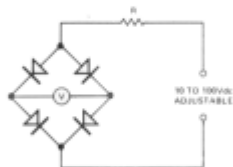
Test requirement for V_{FM} and t_{rr} is as shown below; all leads should be as short as possible.



t_{rr} - REVERSE RECOVERY TIME TEST CIRCUIT
 $I_F = I_R = I_{rr} = 0.1 I_F$

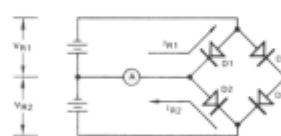


ΔV_F BRIDGE MATCHING CIRCUIT



- NOTES:
- R varies depending on the current range. For the most often used current ranges, R is as follows:
- | Current Range (amperes) | R (ohms) |
|-----------------------------|------------|
| 10^{-5} to 10^{-4} | 10^6 |
| 10^{-4} to 10^{-3} | 10^5 |
| 10^{-3} to 10^{-2} | 10^4 |
| 10^{-2} to 10^{-1} | 10^3 |
| or 10^{-n} to 10^{-n+1} | 10^{n+1} |
- V indicates mismatch of assembly.

ΔI_R BRIDGE MATCHING CIRCUIT



- NOTES:
- $V_{R2} = V_{R1} \pm 1\%$.
 - $I_{R2} - I_{R1} = \Delta I_R$ (difference in I_R between diodes D1 & D2). To measure diodes D3 & D4, reverse cathode-anode terminal connections.
 - A is a center reading pico ammeter. ΔI_R indicated directly on A.